

IN THE SPECIFICATION

Please amend Page 9, Lines 12-20 [Paragraph 0030] as follows:

FIGURE 1 illustrates a prior art structure 100 of a semiconductor device in which a via is to be formed. Prior art structure 100 comprises a substrate 110. A metal layer 120 is placed on the substrate 110. Metal layer 120 serves as an interconnect metal that will connect the via (not shown in FIGURE 1) to other portions of the semiconductor device. An anti-reflective coating (ARC) titanium nitride (TiN) layer 130 is then placed on metal layer 120. A dielectric layer (e.g., silicon dioxide) is then placed on the ~~ART Tin~~ ARC TiN layer 130.